

AP2502

General Description

The AP2502 is a 4-channel independent linear current sink with low dropout voltage and perfect match between each channel. Each channel can provide 20mA continuous constant current.

In application, there is only one $0.1\mu F$ ceramic capacitor required, and there is no any EMI and switching noise issue. It is perfect choice for hand-hold portable system especially based on Li-ion/Polymer battery powered display module.

The brightness can be controlled and/or adjustable via simple PWM signal applied to EN pin.

The AP2502 is available with SOT-23-6 and TSOT-23-6 packages.

Features

- Current Matching Between Each Channel: ±1%
- Low Dropout Voltage: 65mV (Typ.) @ I_{LED}= 20mA
- Maximum Output Current on Each Channel: 20mA
- Ultra-low Quiescent Current: 125µA (Typ.)
- Ultra-low Shutdown Current: 1µA (Max.)
- None EMI and Switching Noise Issue
- Permitted PWM Dimming Frequency up to 150kHz
- OTSD Protection

Applications

- Mobile Phone, Smart Phone, PDA
- MP3, MP4, PMP
- Small Size Backlight Module

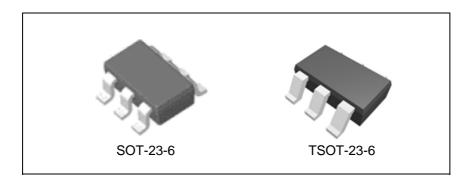


Figure 1. Package Types of AP2502



AP2502

Pin Configuration

K/KT Package (SOT-23-6/TSOT-23-6)

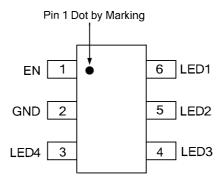


Figure 2. Pin Configuration of AP2502 (Top View)

Pin Descriptions

P in Number	Pin Name	Description		
1	EN	Chip enable pin, active high to permit PWM signal input for brightness control by changing duty cycle		
2	GND	GND		
3, 4, 5, 6	LED4 to LED1	LED cathode terminal for channel number		



AP2502

Functional Block Diagram

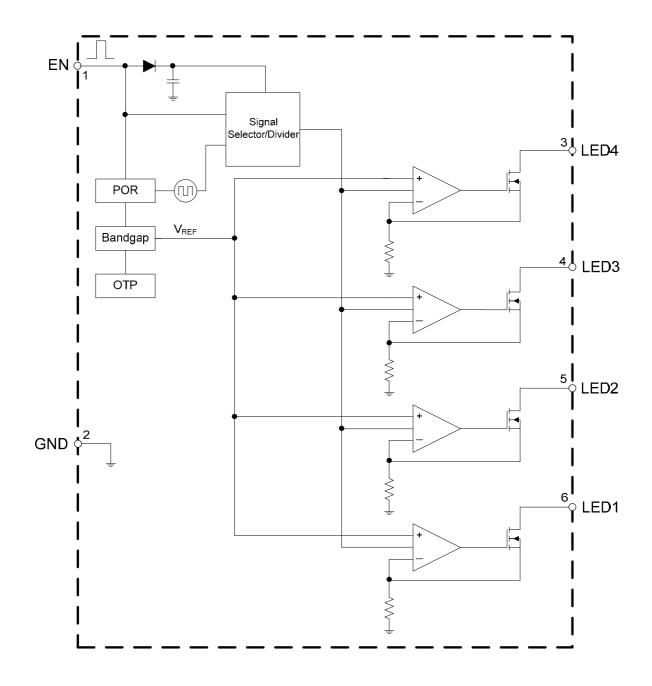
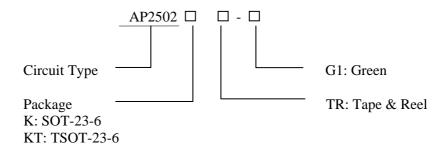


Figure 3. Functional Block Diagram of AP2502



AP2502

Ordering Information



Temperature Packing Package Part Number Marking ID Range **Type** SOT-23-6 -40 to 85°C Tape & Reel AP2502KTR-G1 **GEE** TSOT-23-6 -40 to 85°C AP2502KTTR-G1 L7E Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "G1" suffix in the part number, are RoHS compliant and Green.

Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit	
Enable Input Voltage	V_{EN}	-0.3 to 6.5	V	
Thermal Resistance (Junction to Ambient)	θ_{JA}	250	°C/W	
Operating Junction Temperature Range	$T_{ m J}$	150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	T_{STG}	-65 to 150	°C	
Lead Temperature (Soldering,10 seconds)	T_{LEAD}	260	°C	
ESD (Machine Model)		600	V	
ESD (Human Body Model)		6000	V	

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.



AP2502

Recommended Operating Conditions

Parameter	Symbol	Va	Unit		
rarameter	Symbol	Min	Max	Unit	
Enable Input Voltage	$V_{\rm EN}$	2.0	6.0	V	
Operating Temperature Range	T_{A}	-40	85	°C	
Sink Current	I_{LED}		20	mA	

Electrical Characteristics

 V_{IN} =3.6V, V_{F_LED} =3.2V, T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
LED Dropout Voltage	$V_{DROPOUT}$	I _{SINK} =20mA		65	120	mV
Enable PIN High Voltage	V_{IH}		2		6	V
Enable PIN Low Voltage	$V_{\rm IL}$		0		0.5	V
LED Maximum Sink Current	I _{LED(MAX)}	V _{CC} =3.3 to 6.0V, Enable=V _{CC}	18	20	22	mA
Sink Current Matching Between each Channel	I _{LED-MATCH}	V _{LED} =0.4V		0.5	1	%
Quiescent Current	I_Q	$I_{LED1}=I_{LED2}=I_{LED3}=I_{LED4}=20\text{mA}$		125	180	μΑ
Shutdown Current	I _{SHUTDOWN}	Set EN Pin Low		0.1	1	μА
Thermal Resistance (Junction to Case)	$\theta_{ m JC}$			80		°C/W
PWM Frequency to Adjust Brightness	f_{PWM}				150	kHz
EN Pin Pulse High Time	T_{HIGH}		1			μs
EN Pin Pulse Low Time	T_{LOW}		100			ns
Thermal Shutdown Temperature	T_{OTSD}			150		°C
Thermal Shutdown Hysteresis	T_{HYOTSD}			25		C



AP2502

Typical Performance Characteristics

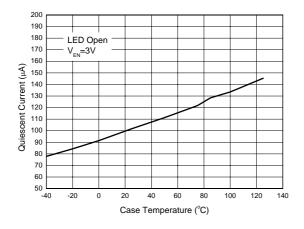
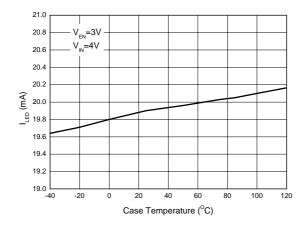


Figure 4. Quiescent Current vs. Case Temperature

Figure 5. Quiescent Current vs. Enable Voltage



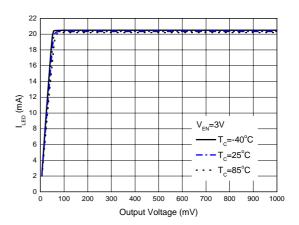


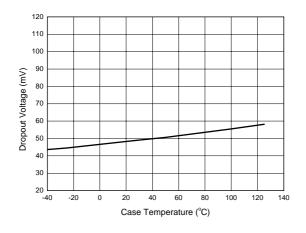
Figure 6. LED Current vs. Case Temperature

Figure 7. LED Current vs. Output Voltage



AP2502

Typical Performance Characteristics (Continued)



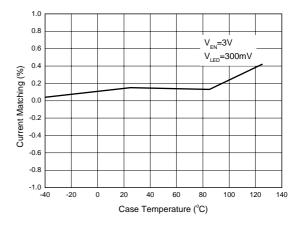
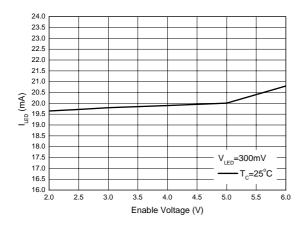


Figure 8. Dropout Voltage vs. Case Temperature

Figure 9. Current Matching vs. Case Temperature



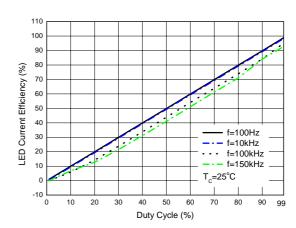


Figure 10. LED Current vs. Enable Voltage

Figure 11. LED Current Efficiency vs. Duty Cycle



AP2502

Typical Performance Characteristics (Continued)

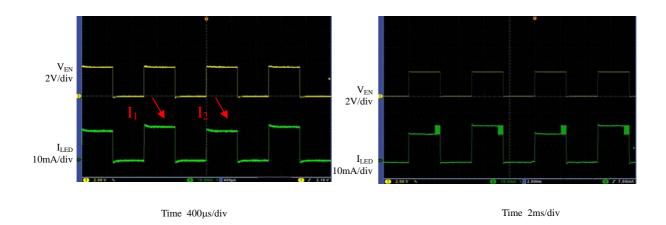


Figure 12. LED Current (Note 2)

(V_{IN} =4V, V_{EN} =0 to 3.6V, Duty cycle=50%, f_{PWM} =1kHz)

Figure 13. Internal Oscillator Working at Low Frequency (V_{IN}=4V, V_{EN}=0 to 3.6V, Duty cycle=50%, f_{PWM}=0.1kHz)

Note 2: Chopper offset-canceling technology is adopted to get good current matching, $I_{LED} = [(I_1 + I_2)/2]*duty$.



AP2502

Typical Application

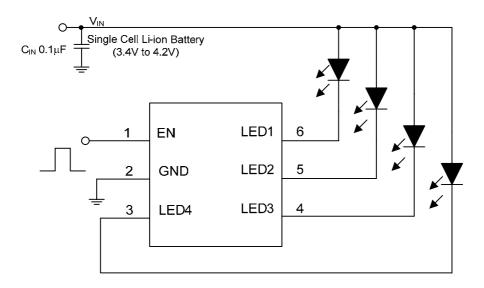


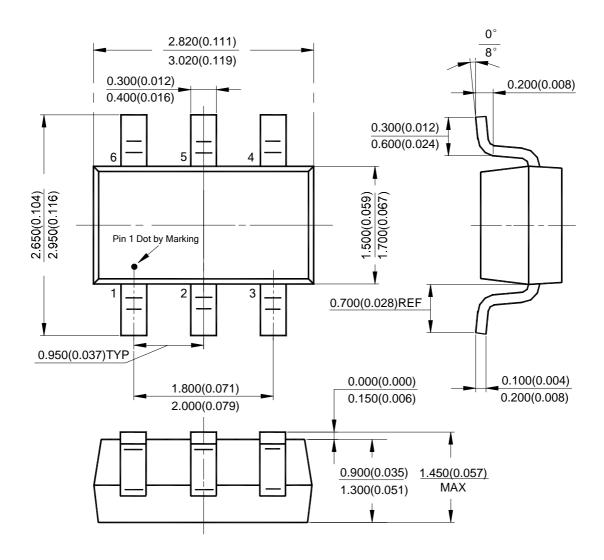
Figure 14. AP2502 Typical Application



AP2502

Mechanical Dimensions

SOT-23-6 Unit: mm(inch)



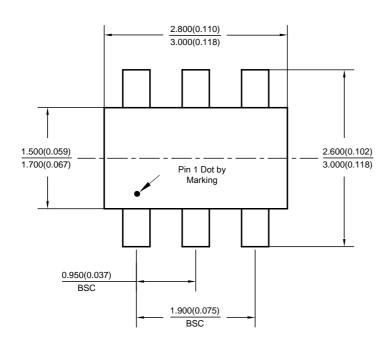


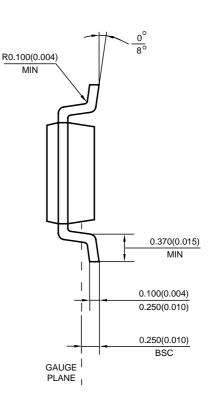
AP2502

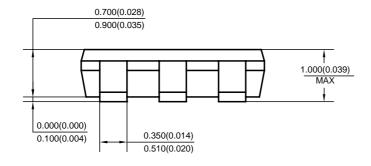
Mechanical Dimensions (Continued)

TSOT-23-6

Unit: mm(inch)











BCD Semiconductor Manufacturing Limited

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